

SI8830

Dual N-Channel Enhancement Mode MOSFET

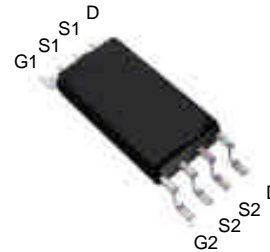
Features

- 20V/6A,
 - $R_{DS(ON)} = 20m\Omega(\text{typ.}) @ V_{GS} = 10V$
 - $R_{DS(ON)} = 23m\Omega(\text{typ.}) @ V_{GS} = 4.5V$
 - $R_{DS(ON)} = 27m\Omega(\text{typ.}) @ V_{GS} = 3.1V$
 - $R_{DS(ON)} = 30m\Omega(\text{typ.}) @ V_{GS} = 2.5V$
 - $R_{DS(ON)} = 42m\Omega(\text{typ.}) @ V_{GS} = 1.8V$
- Super High Dense Cell Design
- Reliable and Rugged
- ESD Protected
- Lead Free and Green Devices Available (RoHS Compliant)

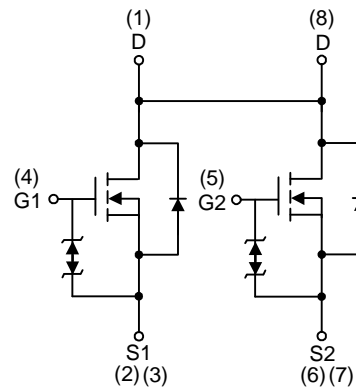
Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems.

Pin Description




Top View of TSSOP-8



N-Channel MOSFET

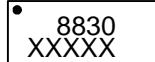
Ordering and Marking Information

SI8830 -  Assembly Material

Package : TSSOP8

TR : Tape & Reel
 Assembly Material
 L : Halogen and Lead Free Device

SI8830 :



XXXXX - Date Code

Note : SI lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. SI lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020D for MSL classification at lead-free peak reflow temperature. SI defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

SI reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

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Absolute Maximum Ratings $(T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Unit	
V_{DSS}	Drain-Source Voltage	20	V	
V_{GSS}	Gate-Source Voltage	± 12		
I_D	Continue Drain Current	6	A	
I_{DM}	300 μs Pulsed Drain Current			20
I_S	Diode continuous forward current	1.5	A	
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$	
T_{STG}	Storage Temperature Range	-55 to 150		
P_D	Maximum Power Dissipation	$T_A=25^\circ\text{C}$	1.25	W
		$T_A=100^\circ\text{C}$	0.5	
$R_{\theta JA}^*$	Thermal Resistance-Junction to Ambient	100	$^\circ\text{C}/\text{W}$	

Note : *Surface Mounted on 1in² pad area, $t \leq 10\text{sec}$.

Electrical Characteristics $(T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	SI 8830			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}, I_{DS}=250\mu\text{A}$	20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=16\text{V}, V_{GS}=0\text{V}$	-	-	1	μA
		$T_J=85^\circ\text{C}$	-	-	30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu\text{A}$	0.4	0.7	1	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 10\text{V}, V_{DS}=0\text{V}$	-	-	± 10	μA
$R_{DS(ON)}^a$	Drain-Source On-state Resistance	$V_{GS}=10\text{V}, I_{DS}=6\text{A}$	16	20	27	m Ω
		$V_{GS}=4.5\text{V}, I_{DS}=5\text{A}$	19	23	30	
		$V_{GS}=3.1\text{V}, I_{DS}=4\text{A}$	22	27	35	
		$V_{GS}=2.5\text{V}, I_{DS}=4\text{A}$	25	30	39	
		$V_{GS}=1.8\text{V}, I_{DS}=2\text{A}$	32	42	55	
Diode Characteristics						
V_{SD}^a	Diode Forward Voltage	$I_{SD}=1.5\text{A}, V_{GS}=0\text{V}$	-	0.7	1.3	V
t_{rr}	Reverse Recovery Time	$I_{SD}=6\text{A}, dI_{SD}/dt=100\text{A}/\mu\text{s}$	-	15	-	nS
Q_{rr}	Reverse Recovery Charge		-	7	-	nC

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Electrical Characteristics (Cont.) (T_A = 25°C unless otherwise noted)

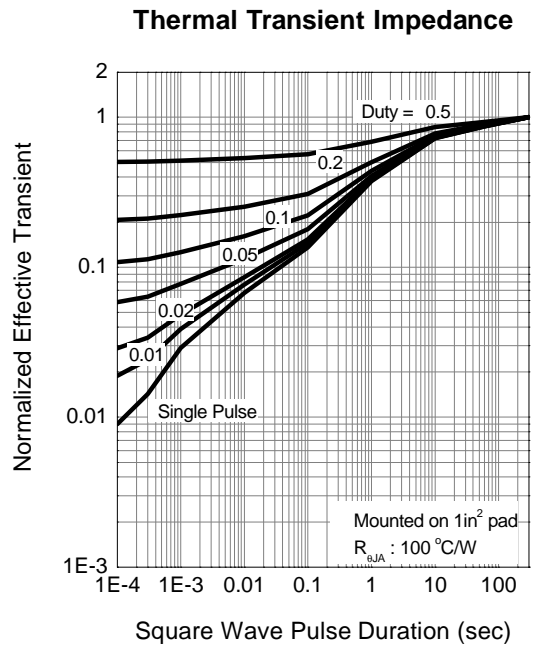
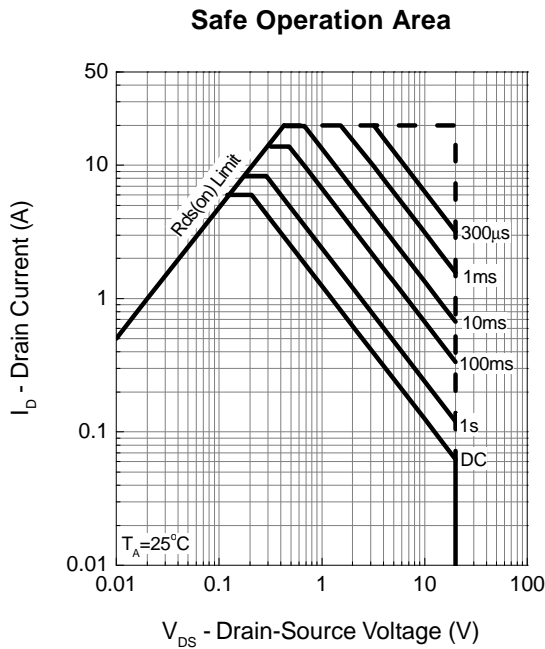
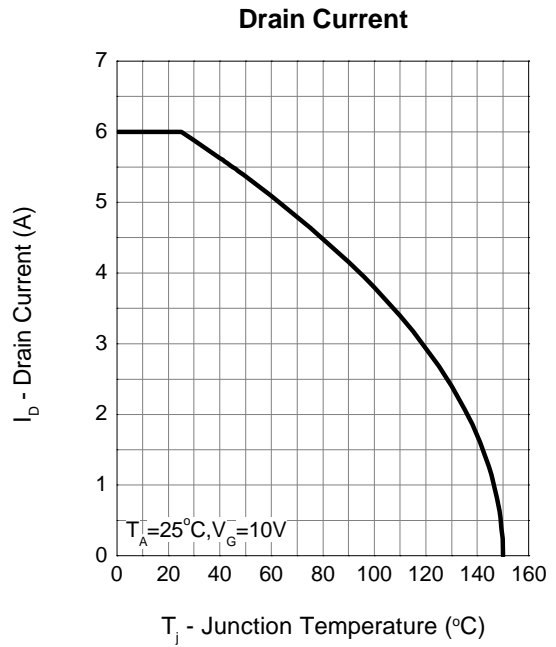
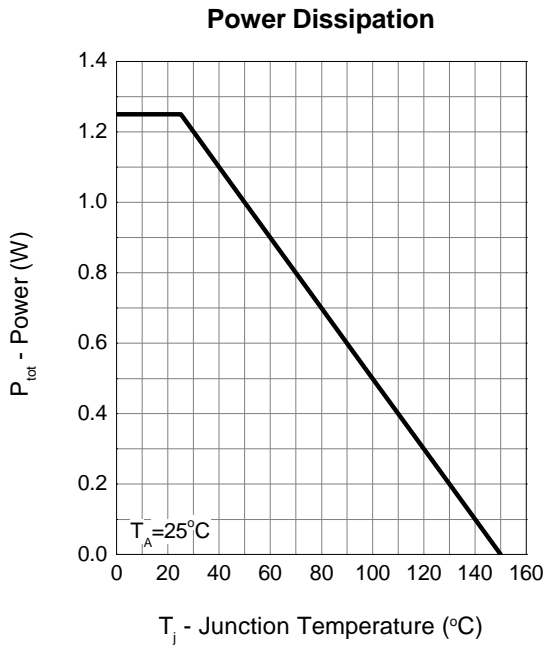
Symbol	Parameter	Test Conditions	SI 8830			Unit
			Min.	Typ.	Max.	
Dynamic Characteristics ^b						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	4	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =10V, Frequency=1.0MHz	-	550	-	pF
C _{oss}	Output Capacitance		-	100	-	
C _{rss}	Reverse Transfer Capacitance		-	85	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =10V, R _L =10Ω, I _{DS} =1A, V _{GEN} =4.5V, R _G =6Ω	-	5	10	ns
t _r	Turn-on Rise Time		-	15	26	
t _{d(OFF)}	Turn-off Delay Time		-	30	55	
t _f	Turn-off Fall Time		-	5	10	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =10V, V _{GS} =4.5V, I _{DS} =6A	-	8.8	12	nC
Q _{gs}	Gate-Source Charge		-	0.8	-	
Q _{gd}	Gate-Drain Charge		-	3.3	-	

Note a : Pulse test ; pulse width ≤ 300μs, duty cycle ≤ 2%.

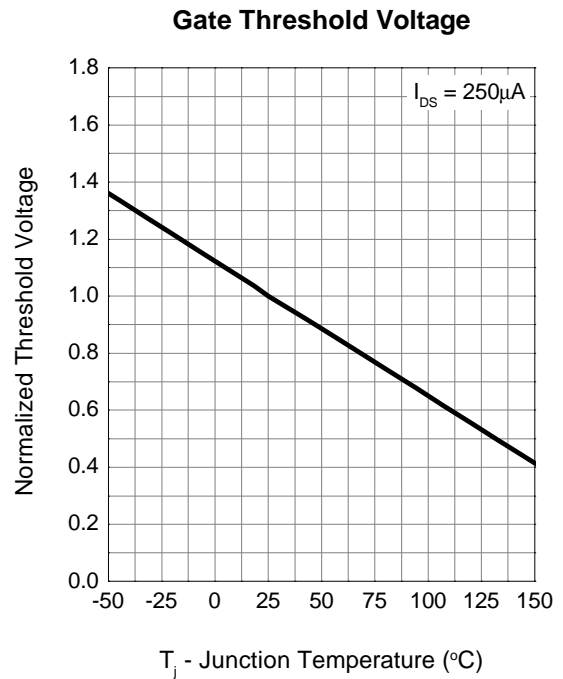
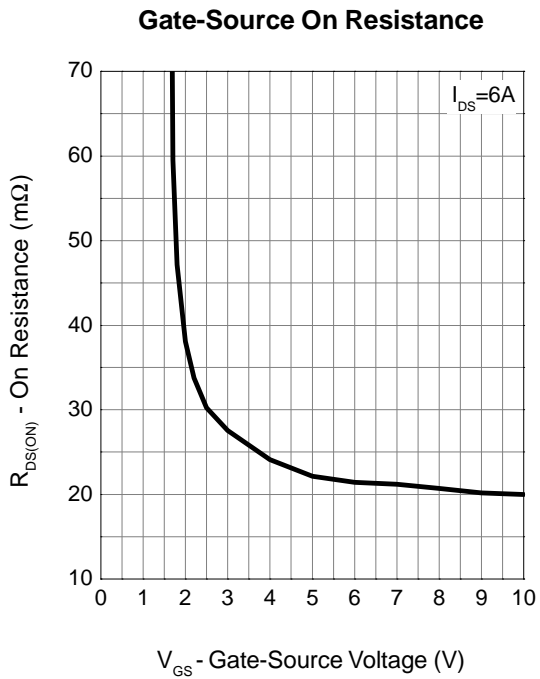
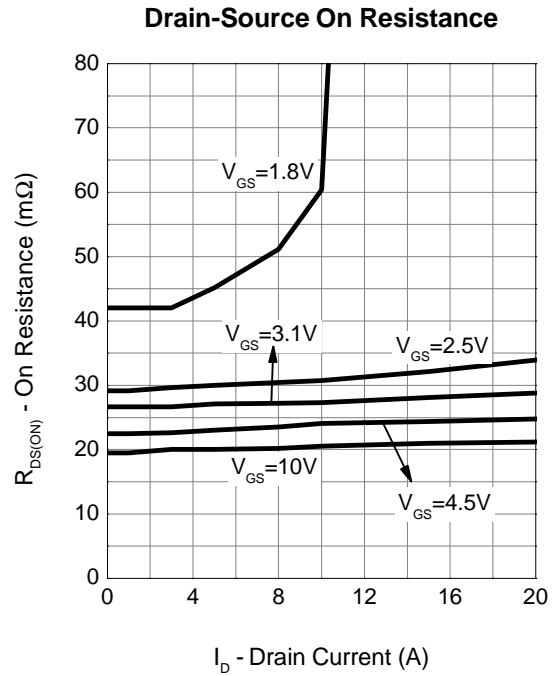
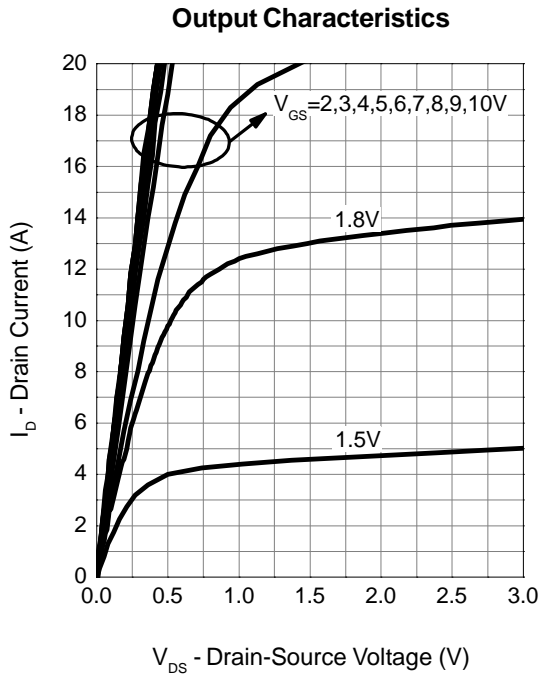
Note b : Guaranteed by design, not subject to production testing.

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Typical Operating Characteristics

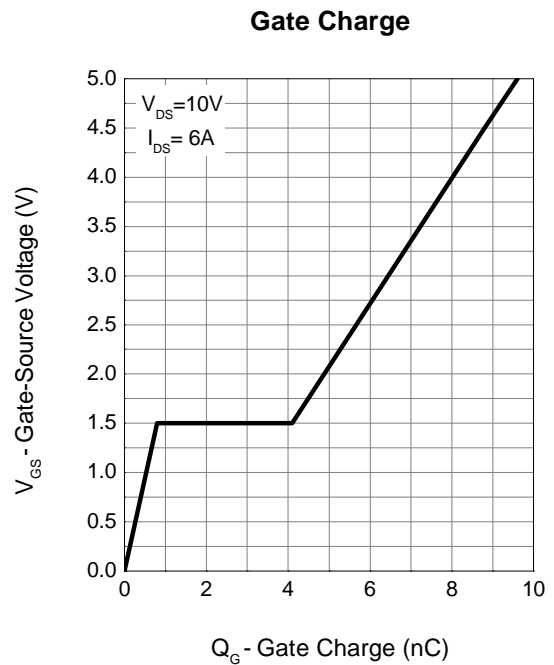
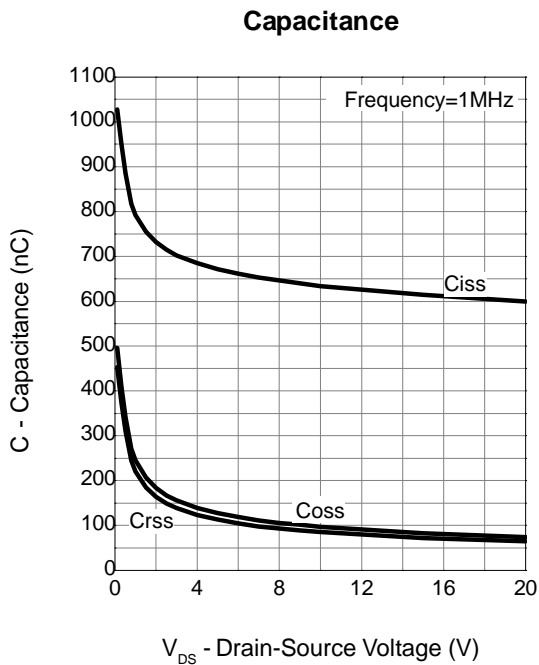
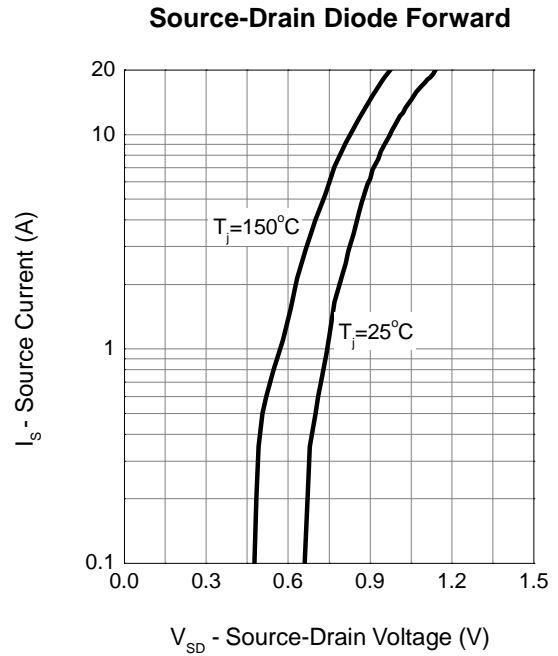
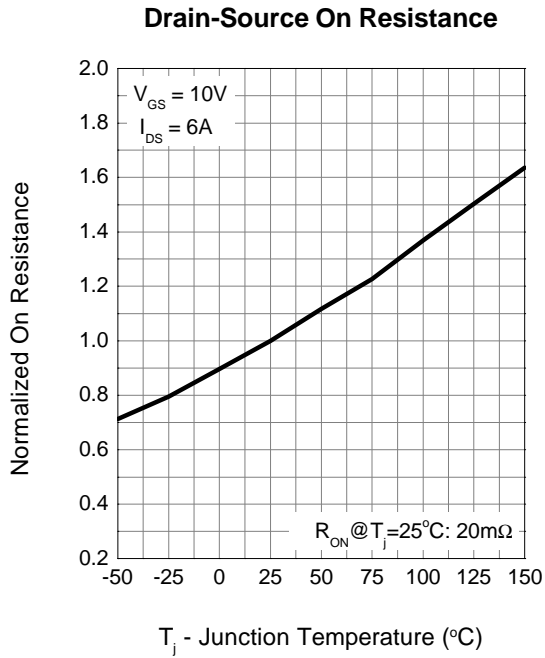


Typical Operating Characteristics (Cont.)



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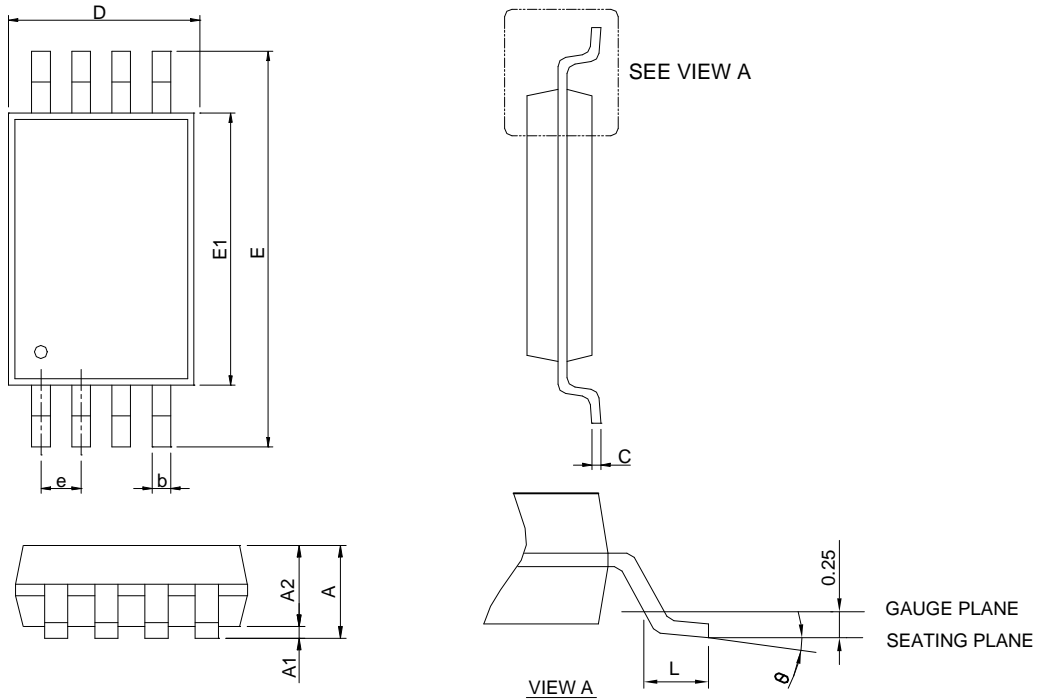
Typical Operating Characteristics (Cont.)



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Package Information

TSSOP-8



SYMBOL	TSSOP-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A		1.20		0.047
A1	0.05	0.15	0.002	0.006
A2	0.80	1.05	0.031	0.041
b	0.19	0.30	0.007	0.012
c	0.09	0.20	0.004	0.008
D	2.90	3.10	0.114	0.122
E	6.20	6.60	0.244	0.260
E1	4.30	4.50	0.169	0.177
e	0.65 BSC		0.026 BSC	
L	0.45	0.75	0.018	0.030
θ	0°	8°	0°	8°

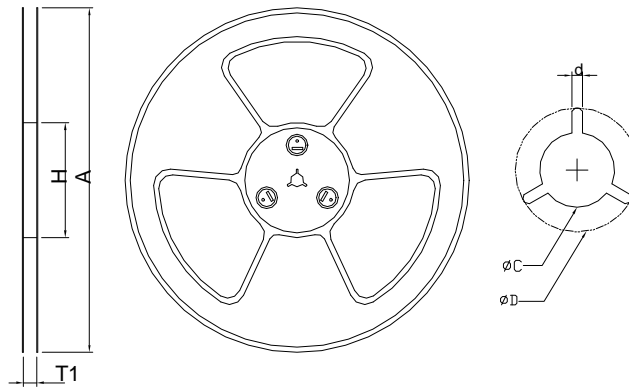
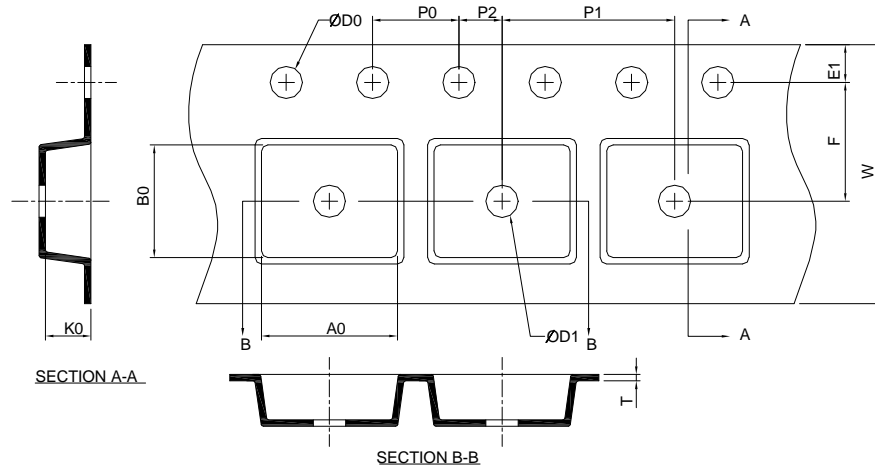
Note : 1. Follow JEDEC MO-153 AA

2. Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 6 mil per side.

3. Dimension "E1" does not include inter-lead flash or protrusions. Inter-lead flash and protrusions shall not exceed 10 mil per side.

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Carrier Tape & Reel Dimensions



Application	A	H	T1	C	d	D	W	E1	F
TSSOP-8	330.0 ±2.00	50 MIN.	12.4+2.00 -0.00	13.0+0.50 -0.20	1.5 MIN.	20.2 MIN.	12.0 ±0.30	1.75 ±0.10	5.5 ±0.10
	P0	P1	P2	D0	D1	T	A0	B0	K0
	4.00 ±0.10	8.00 ±0.10	2.00 ±0.05	1.5+0.10 -0.00	1.5 MIN.	0.6+0.00 -0.40	6.90 ±0.20	3.40 ±0.20	1.60 ±0.20

(mm)

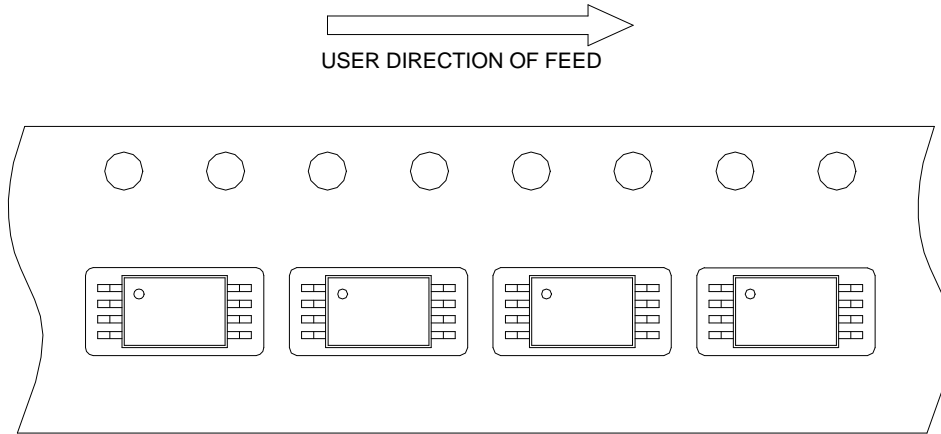
Devices Per Unit

Package Type	Unit	Quantity
TSSOP- 8	Tape & Reel	3000

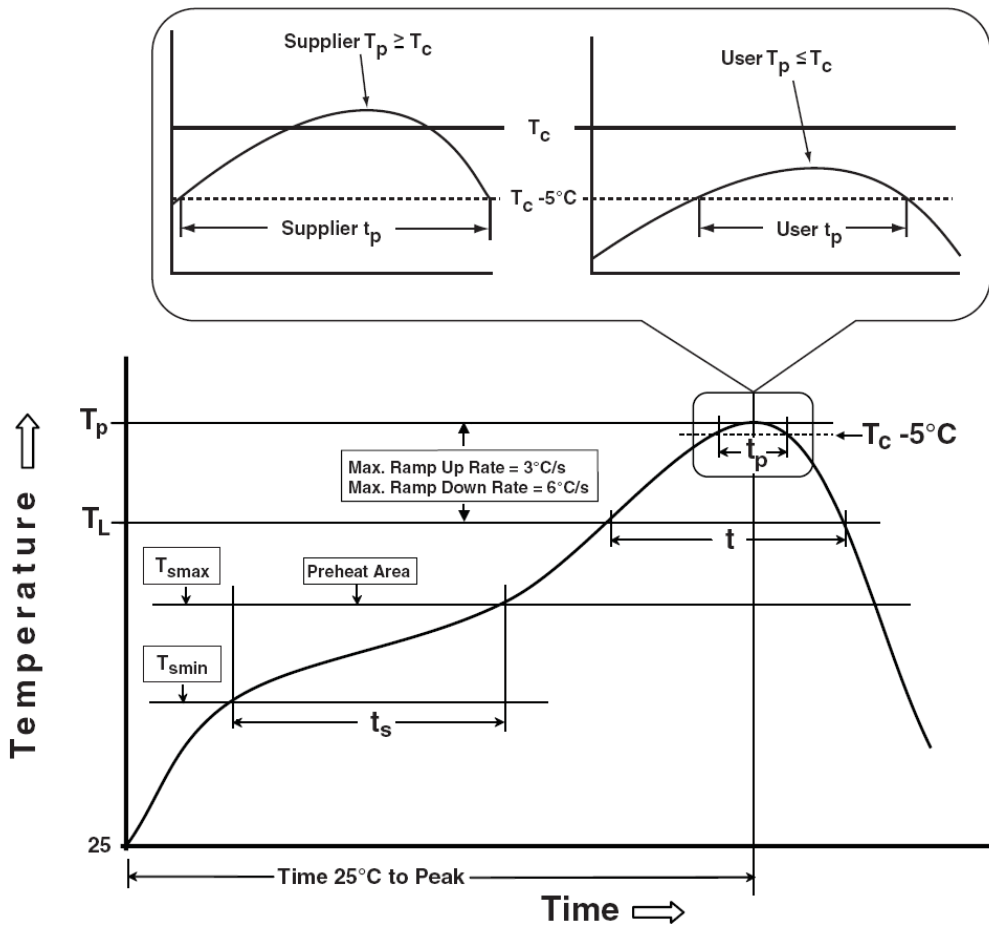
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Taping Direction Information

TSSOP-8



Classification Profile



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Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum.		
** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HOLT	JESD-22, A108	1000 Hrs, Bias @ 125°C
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C